



501.42841X00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): KUMAGAI, et al.
Serial No.: 10/625,616
Filed: July 24, 2003
For: SEMICONDUCTOR DEVICE INCLUDING N-CHANNELED
FETs AND P-CHANNELED FETs WITH IMPROVED DRAIN
CURRENT CHARACTERISTICS (As Amended)
Group: 2811 Exr. H. Vu

AMENDMENT

Commissioner of Patents
POB 1450
Alexandria, VA 22313-1450

August 3, 2005

Sir:

In response to the Office Action dated May 3, 2005, please amend the above-identified application as listed below and as set forth on the following pages:

Amendments to the Title;

Amendments to the Claims; and

Remarks are included following the amendments.